- Trimmed Offset Voltage:
  - TLC279 . . . 900  $\mu$ V Max at 25°C, V<sub>DD</sub> = 5 V
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over Specified Temperature Range:

0°C to 70°C . . . 3 V to 16 V -40°C to 85°C . . . 4 V to 16 V -55°C to 125°C . . . 4 V to 16 V

- Single-Supply Operation
- Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix and I-Suffix Versions)
- Low Noise . . . Typically 25 nV/√Hz at f = 1 kHz
- Output Voltage Range Includes Negative Rail
- High Input Impedance . . .  $10^{12} \Omega$  Typ
- ESD-Protection Circuitry
- Small-Outline Package Option Also Available in Tape and Reel
- Designed-In Latch-Up Immunity

## description

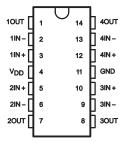
The TLC274 and TLC279 quad operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, low noise, and speeds approaching that of general-purpose BiFET devices.

These devices use Texas Instruments silicongate LinCMOS™ technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

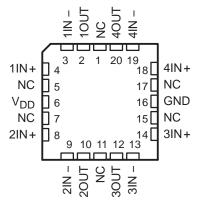
The extremely high input impedance, low bias currents, and high slew rates make these cost-effective devices ideal for applications which have previously been reserved for BiFET and NFET products. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC274 (10 mV) to the high-precision TLC279 (900  $\mu\text{V}$ ). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

LinCMOS is a trademark of Texas Instruments.

## D, J, N, OR PW PACKAGE (TOP VIEW)

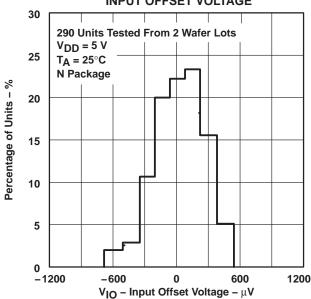


### FK PACKAGE (TOP VIEW)



NC - No internal connection

## DISTRIBUTION OF TLC279 INPUT OFFSET VOLTAGE



SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## description (continued)

In general, many features associated with bipolar technology are available on LinCMOS™ operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC274 and TLC279. The devices also exhibit low voltage single-supply operation, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up.

The TLC274 and TLC279 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from  $0^{\circ}$ C to  $70^{\circ}$ C. The I-suffix devices are characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C. The M-suffix devices are characterized for operation over the full military temperature range of  $-55^{\circ}$ C to  $125^{\circ}$ C.

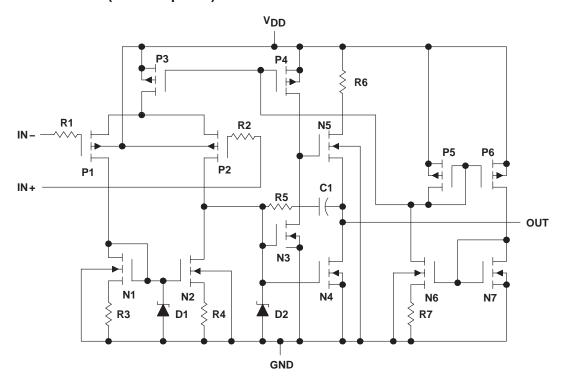
### **AVAILABLE OPTIONS**

			PA	CKAGED DEV	ICES		CUID
TA	V <sub>IO</sub> max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	CHIP FORM (Y)
0°C to 70°C	900 μV 2 mV 5 mV 10 mV	TLC279CD TLC274BCD TLC274ACD TLC274CD	  -  -		TLC279CN TLC274BCN TLC274ACN TLC274CN	   TLC274CPW	   TLC274Y
-40°C to 85°C	900 μV 2 mV 5 mV 10 mV	TLC279ID TLC274BID TLC274AID TLC274ID	1111	1111	TLC279IN TLC274BIN TLC274AIN TLC274IN		
−55°C to 125°C	900 μV 10 mV	TLC279MD TLC274MD	TLC279MFK TLC274MFK	TLC279MJ TLC274MJ	TLC279MN TLC274MN	_ _	_ _

The D package is available taped and reeled. Add R suffix to the device type (e.g., TLC279CDR).

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

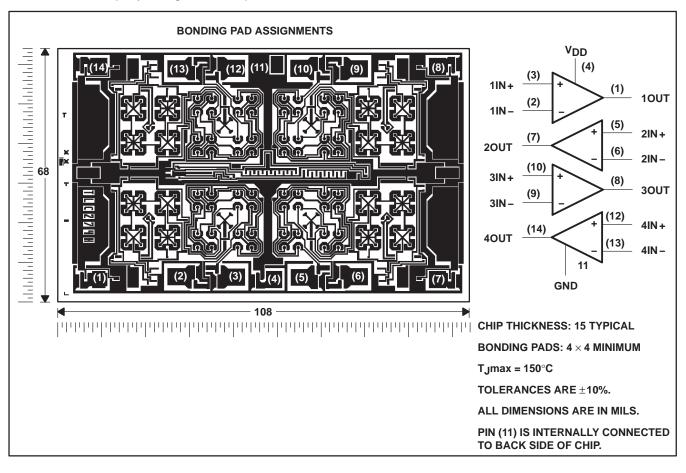
## equivalent schematic (each amplifier)



SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## **TLC274Y chip information**

These chips, when properly assembled, display characteristics similar to the TLC274C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage, V <sub>DD</sub> (see Note 1)	
Differential input voltage, V <sub>ID</sub> (see Note 2)	±V <sub>DD</sub>
Input voltage range, V <sub>I</sub> (any input)	–0.3 V to V <sub>DD</sub>
Input current, I <sub>1</sub>	
Output current, I <sub>O</sub> (each output)	±30 mA
Total current into V <sub>DD</sub>	
Total current out of GND	
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Continuous total dissipation Operating free-air temperature, T <sub>A</sub> : C suffix	
·	0°C to 70°C
Operating free-air temperature, T <sub>A</sub> : C suffix	0°C to 70°C 40°C to 85°C
Operating free-air temperature, T <sub>A</sub> : C suffix	
Operating free-air temperature, T <sub>A</sub> : C suffix	
Operating free-air temperature, T <sub>A</sub> : C suffix  I suffix  M suffix  Storage temperature range	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
  - 2. Differential voltages are at the noninverting input with respect to the inverting input.
  - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	_
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
N	1575 mW	12.6 mW/°C	1008 mW	819 mW	_
PW	700 mW	5.6 mW/°C	448 mW	_	_

## recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SU	FFIX	
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V <sub>DD</sub>		3	16	4	16	4	16	V
Common de la contratta de V	V <sub>DD</sub> = 5 V	-0.2	3.5	-0.2	3.5	0	3.5	.,
Common-mode input voltage, V <sub>IC</sub>	V <sub>DD</sub> = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	°C

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T <sub>A</sub> †	TLC274 TLC274			UNIT
						MIN	TYP	MAX	
		TI 00740	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC274C	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			12	>/
		TI 007440	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	mV
l.,	Lamest affect wells as	TLC274AC	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			6.5	
VIO	Input offset voltage	TI 0074D0	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		340	2000	
		TLC274BC	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			3000	
		TI 00700	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0$ ,	25°C		320	900	μV
		TLC279C	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			1500	
αΛΙΟ	Average temperature coeffic offset voltage	ient of input			25°C to 70°C		1.8		μV/°C
	lanut effect summent (e.e. Net	- 4\			25°C		0.1	60	A
liO	Input offset current (see Note	e 4)	V 05.V	V 05V	70°C		7	300	рA
	1	4)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 \text{ V}$	25°C		0.6	60	
IВ	Input bias current (see Note	4)			70°C		40	600	рA
						-0.2	-0.3		
					25°C	to 4	to		V
VICR	Common-mode input voltage (see Note 5)	e range					4.2		
	(see Note 3)				Full range	-0.2 to			V
					l am ramiga	3.5			-
					25°C	3.2	3.8		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	0°C	3	3.8		V
					70°C	3	3.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	5	23		
AVD	Large-signal differential volta amplification	age	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 10 \text{ k}\Omega$	0°C	4	27		V/mV
	amplification				70°C	4	20		
					25°C	65	80		
CMRR	Common-mode rejection rati	io	V <sub>IC</sub> = V <sub>ICR</sub> min		0°C	60	84		dB
					70°C	60	85		
		_			25°C	65	95		
ksvr	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	0	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	94		dB
	(¬, DD, ¬, IO)				70°C	60	96		<u></u>
			l		25°C		2.7	6.4	
IDD	Supply current (four amplifie	rs)	V <sub>O</sub> = 2.5 V, No load	$V_{IC} = 2.5 V,$	0°C		3.1	7.2	mA
1			140 1000		70°C		2.3	5.2	

† Full range is 0°C to 70°C.

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics at specified free-air temperature, $V_{DD}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T <sub>A</sub> †	TLC274 TLC274			UNIT
						MIN	TYP	MAX	
		TI 00740	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC274C	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			12	
		TI 007440	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	mV
.,	land of a first colland	TLC274AC	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			6.5	
VIO	Input offset voltage	TI 007.100	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		390	2000	
		TLC274BC	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			3000	
		TI 00700	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		370	1200	μV
		TLC279C	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			1900	
αΛΙΟ	Average temperature co	efficient of			25°C to 70°C		2		μV/°C
					25°C		0.1	60	
IIO	Input offset current (see	Note 4)			70°C		7	300	рA
			V <sub>O</sub> =.5 V,	$V_{IC} = 5 V$	25°C		0.7	60	
I <sub>IB</sub>	Input bias current (see I	Note 4)			70°C		50	600	pA
					25°C	-0.2 to	-0.3 to		V
\/·	Common-mode input vo	ommon-mode input voltage range			9	9.2			
VICR	(see Note 5)				F	-0.2			
					Full range	to 8.5			V
					25°C	8	8.5		
Vон	High-level output voltage	е	$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	0°C	7.8	8.5		V
					70°C	7.8	8.4		
					25°C		0	50	
VOL	Low-level output voltage	e	$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	10	36		
$A_{VD}$	Large-signal differential amplification	voltage	$V_0 = 1 \ V \ to 6 \ V,$	$R_L = 10 \text{ k}\Omega$	0°C	7.5	42		V/mV
	ampimoation				70°C	7.5	32		
					25°C	65	85		
CMRR	Common-mode rejection	n ratio	V <sub>IC</sub> = V <sub>ICR</sub> min		0°C	60	88		dB
					70°C	60	88		
					25°C	65	95		
k <sub>SVR</sub>	Supply-voltage rejection (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	94		dB
	(\(\text{\O}\) \(\text{\O}\)			-	70°C	60	96		
					25°C		3.8	8	
I <sub>DD</sub>	Supply current (four am	plifiers)	V <sub>O</sub> = 5 V, No load	$V_{IC} = 5 V$	0°C		4.5	8.8	mA
			INO IOAU		70°C		3.2	6.8	

<sup>†</sup> Full range is 0°C to 70°C.

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics at specified free-air temperature, $V_{DD}$ = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T <sub>A</sub> †		4I, TLC2 4BI, TL0	-	UNIT
						MIN	TYP	MAX	
		TI 00741	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC274I	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			13	>/
		TI 007441	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	mV
l.,		TLC274AI	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			7	
VIO	Input offset voltage	TI 007 (D)	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		340	2000	
		TLC274BI	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			3500	.,
		TI 00701	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		320	900	μV
		TLC279I	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			2000	
ανιο	Average temperature coefficient voltage	ficient of input			25°C to 85°C		1.8		μV/°C
					25°C		0.1	60	
lio	Input offset current (see N	lote 4)			85°C		24	1000	рA
			$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	25°C		0.6	60	
I <sub>IB</sub>	Input bias current (see No	te 4)			85°C		200	2000	рA
	Common-mode input volta	age range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	-0.2 to 3.5			V
					25°C	3.2	3.8		
Vон	High-level output voltage		V <sub>ID</sub> = 100 mV,	$R_L = 10 \text{ k}\Omega$	-40°C	3	3.8		V
				_	85°C	3	3.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	5	23		
AVD	Large-signal differential vo amplification	oltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 10 \text{ k}\Omega$	-40°C	3.5	32		V/mV
	amplification				85°C	3.5	19		
					25°C	65	80		
CMRR	Common-mode rejection	atio	V <sub>IC</sub> = V <sub>ICR</sub> min		-40°C	60	81		dB
					85°C	60	86		
					25°C	65	95		
ksvr	Supply-voltage rejection ra (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V <sub>O</sub> = 1.4 V	-40°C	60	92		dB
	(\(\times \D\) \(\times \D\)				85°C	60	96		
			<u> </u>		25°C		2.7	6.4	
$I_{DD}$	Supply current (four ampli	fiers)	$V_O = 2.5 \text{ V},$ No load	$V_{IC} = 2.5 V,$	-40°C		3.8	8.8	mA
			140 1000		85°C		2.1	4.8	

<sup>†</sup>Full range is –40°C to 85°C.

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics at specified free-air temperature, $V_{DD}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T <sub>A</sub> †		4I, TLC2 4BI, TL		UNIT
						MIN	TYP	MAX	
		TI 00741	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC274I	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			13	>/
		TI 007441	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	mV
.,	land Markovitana	TLC274AI	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			7	
VIO	Input offset voltage	TI 0074DI	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		390	2000	
		TLC274BI	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			3500	
		TI 00701	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		370	1200	μV
		TLC279I	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			2900	
ανιο	Average temperature coefficient offset voltage	ent of input			25°C to 85°C		2		μV/°C
					25°C		0.1	60	
liO	Input offset current (see Note	4)			85°C		26	1000	pA
			$V_0 = 5 V$ ,	$V_{IC} = 5 V$	25°C		0.7	60	
IIB	Input bias current (see Note 4	4)			85°C		220	2000	рA
					1	-0.2	-0.3		
					25°C	to	to		V
VICR	Common-mode input voltage (see Note 5)	range				9	9.2		
10.1	(see Note 5)				Full range	-0.2 to			V
					T all range	8.5			,
					25°C	8	8.5		
∨он	High-level output voltage		V <sub>ID</sub> = 100 mV,	$R_L = 10 \text{ k}\Omega$	-40°C	7.8	8.5		V
				_	85°C	7.8	8.5		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	10	36		
AVD	Large-signal differential voltage amplification	ge	$V_{O} = 1 \text{ V to 6 V},$	$R_L = 10 \text{ k}\Omega$	-40°C	7	47		V/mV
	amplification			_	85°C	7	31		
					25°C	65	85		
CMRR	Common-mode rejection ratio	)	V <sub>IC</sub> = V <sub>ICR</sub> min		-40°C	60	87		dB
	•		.5 .5		85°C	60	88		
					25°C	65	95		
ksvr	Supply-voltage rejection ratio		$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V <sub>O</sub> = 1.4 V	-40°C	60	92		dB
	$(\Delta V_{DD}/\Delta V_{IO})$			Ū	85°C	60	96		
					25°C		3.8	8	
I <sub>DD</sub>	Supply current (four amplifier	s)	$V_0 = 5 V$	$V_{IC} = 5 V$	-40°C		5.5	10	mA
	•		No load		85°C		2.9	6.4	

<sup>†</sup>Full range is -40°C to 85°C.

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	DADAMETE -		TEOT	NTIONO	- +	TLC27	4M, TLC	279M	
	PARAMETER		TEST CONE	DITIONS	T <sub>A</sub> †	MIN	TYP	MAX	UNIT
		TLC274M	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	>/
\/	lanut effect valtage	TLC274M	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			12	mV
VIO	Input offset voltage	TI 0070M	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0$ ,	25°C		320	900	
		TLC279M	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			3750	μV
ανιο	Average temperature coefficie offset voltage	nt of input			25°C to 125°C		2.1		μV/°C
1	Input offset surrent (see Note	4)			25°C		0.1	60	рА
IO	Input offset current (see Note	4)	\/_ 2.5.\/	V:- 25V	125°C		1.4	15	nA
1	Innuit bios surrent (see Note 4	,	$V_{O} = 2.5 \text{ V},$	AIC = 5.2 A	25°C		0.6	60	рА
ΙΒ	Input bias current (see Note 4	)			125°C		9	35	nA
	Common-mode input voltage	range			25°C	0 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	-			Full range	0 to 3.5			V
					25°C	3.2	3.8		
∨он	High-level output voltage		V <sub>ID</sub> = 100 mV,	$R_L = 10 \text{ k}\Omega$	−55°C	3	3.8		V
					125°C	3	3.8		
					25°C		0	50	
VoL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
					25°C	5	23		
AVD	Large-signal differential voltage amplification	е	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 10 \text{ k}\Omega$	−55°C	3.5	35		V/mV
	ap.iii.outo				125°C	3.5	16		
					25°C	65	80		
CMRR	Common-mode rejection ratio		VIC = VICRmin		−55°C	60	81		dB
					125°C	60	84		
	Owner beautiful and the state of the state o				25°C	65	95		
ksvr	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )		$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 V$	−55°C	60	90		dB
					125°C	60	97		
			V 05V	V 0.5.V	25°C		2.7	6.4	
I <sub>DD</sub>	Supply current (four amplifiers	)	$V_O = 2.5 \text{ V},$ No load	$V_{IC} = 2.5 V,$	−55°C		4	10	mA
					125°C		1.9	4.4	

<sup>†</sup> Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics at specified free-air temperature, $V_{DD}$ = 10 V (unless) otherwise noted)

					_ +	TLC27	4M, TLC	279M	
	PARAMETER		TEST CONI	DITIONS	T <sub>A</sub> †	MIN	TYP	MAX	UNIT
		TI 007414	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	>/
,	land offers wellen	TLC274M	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			12	mV
VIO	Input offset voltage	TI 0070M	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		370	1200	
		TLC279M	$R_S = 50 \Omega$ ,	$R_L = 10 \text{ k}\Omega$	Full range			4300	μV
αΛΙΟ	Average temperature coefficie offset voltage	ent of input			25°C to 125°C		2.2		μV/°C
1	Innut offeet ourrent (one Note	4)			25°C		0.1	60	pА
lio	Input offset current (see Note	4)	V <sub>O</sub> = 5 V,	\/ <b>  .</b>	125°C		1.8	15	nA
lin.	Input bigg ourrent (age Note 4	١	VO = 2V	$V_{IC} = 5 V$	25°C		0.7	60	рА
IB	Input bias current (see Note 4	)			125°C		10	35	nA
.,	Common-mode input voltage	range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	Ü			Full range	0 to 8.5			V
					25°C	8	8.5		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	−55°C	7.8	8.5		V
					125°C	7.8	8.4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	1				25°C	10	36		
$A_{VD}$	Large-signal differential voltage amplification	je	$V_{O} = 1 \text{ V to 6 V},$	$R_L = 10 \text{ k}\Omega$	−55°C	7	50		V/mV
	атриноалогі				125°C	7	27		
					25°C	65	85		
CMRR	Common-mode rejection ratio		VIC = VICRmin		−55°C	60	87		dB
					125°C	60	86		
					25°C	65	95		
ksvr	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )		$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	90		dB
	(-· UU/ IU/				125°C	60	97		
			.,		25°C		3.8	8	
IDD	Supply current (four amplifiers	s)	V <sub>O</sub> = 5 V, No load	$V_{IC} = 5 V$	−55°C		6.0	12	mA
					125°C		2.5	5.6	

<sup>†</sup>Full range is -55°C to 125°C.

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	TA	TLC274 TL TLC274	C274AC	,	UNIT
					MIN	TYP	MAX	
				25°C		3.6		
			V <sub>IPP</sub> = 1 V	0°C		4		
	Class note at smits nois	$R_L = 10 \Omega$ ,		70°C		3		Miss
SR	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		2.9		V/μs
		3	V <sub>IPP</sub> = 2.5 V	0°C		3.1		
				70°C		2.5		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		25		nV/√ <del>Hz</del>
				25°C		320		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_I = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	0°C		340		kHz
		170 132,	occ rigure r	70°C		260		
				25°C		1.7		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	0°C		2		MHz
		Occ rigure 3		70°C		1.3		
				25°C		46°		
$\phi_{\text{m}}$	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	$f = B_1$	0°C		47°		
		OL - 20 Pr,		70°C		44°		

## operating characteristics at specified free-air temperature, $V_{DD} = 10 \text{ V}$

	PARAMETER	TEST CO	ONDITIONS	TA	TLC274 TL TLC274	C274AC	<b>;</b> ,	UNIT
					MIN	TYP	MAX	
				25°C		5.3		
			V <sub>IPP</sub> = 1 V	0°C		5.9		
CD	Class note at smits main	$R_L = 10 \Omega$ ,		70°C		4.3		Mhia
SR	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		4.6		V/μs
		3	V <sub>IPP</sub> = 5.5 V	0°C		5.1		
				70°C		3.8		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		25		nV/√ <del>Hz</del>
			_	25°C		200		
Вом	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 pF,	0°C		220		kHz
		TC = 10 K32,	Occ rigure r	70°C		140		
				25°C		2.2		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	0°C		2.5		MHz
		occ riguic 3		70°C		1.8		
		.,,	, _	25°C		49°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	0°C		50°		
		OL - 23 Pi,	occ i iguic o	70°C		46°		

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	ONDITIONS	TA	TLC274I, TLC274AI, TLC274BI, TLC279I			UNIT
					MIN	TYP	MAX	
				25°C		3.6		
			V <sub>IPP</sub> = 1 V	-40°C		4.5		
CD.	Class note at waits and	$R_L = 10 \text{ k}\Omega$		85°C		2.8		Mar
SR	Slew rate at unity gain	C <sub>L</sub> = 20 <sub>P</sub> F, See Figure 1		25°C		2.9		V/μs
		J. J.	V <sub>IPP</sub> = 2.5 V	-40°C		3.5		
				85°C		2.3		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		25		nV/√ <del>Hz</del>
				25°C		320		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_I = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 <sub>P</sub> F, See Figure 1	-40°C		380		kHz
		1 TC = 10 K32,	occ rigure r	85°C		250		
				25°C		1.7		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	-40°C		2.6		MHz
		Gee i iguie e		85°C		1.2		
		.,	, 5	25°C		46°		
φm		$V_{I} = 10 \text{ mV},$ $C_{I} = 20 \text{ pF},$		-40°C		49°		
		OL - 20 Pr,	occ i iguic o	85°C		43°		

## operating characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V

	PARAMETER	TEST CO	NDITIONS	TA	TLC274I, TLC274AI, TLC274BI, TLC279I			UNIT
					MIN	TYP	MAX	
				25°C		5.3		
			V <sub>IPP</sub> = 1 V	-40°C		6.7		
SR S	Olements at write main	$R_L = 10 \Omega$ ,		85°C		4		\// -
SK	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		4.6		V/μs
			V <sub>IPP</sub> = 5.5 V	-40°C		5.8		
				85°C		3.5		
٧n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		25		nV/√ <del>Hz</del>
				25°C		200		
Вом	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 <sub>P</sub> F, See Figure 1	-40°C		260		kHz
			See rigure r	85°C		130		
				25°C		2.2		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	-40°C		3.1		MHz
		Gee rigule 3		85°C		1.7		
φm		.,,		25°C		49°		
	Phase margin	$V_{\parallel} = 10 \text{ mV},$ $C_{\perp} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	-40°C		52°		
		OL - 20 PI,	CCC r iguic 3	85°C		46°		

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	DADAMETED	TEOT 00	NIDITION IO	_	TLC274	M, TLC	279M				
	PARAMETER	IESI CO	NDITIONS	TA	MIN	TYP	MAX	UNIT			
				25°C		3.6					
			V <sub>IPP</sub> = 1 V	−55°C		4.7					
	Olements at write and	$R_L = 10 \text{ k}\Omega$		125°C		2.3		\// -			
SR	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		2.9		V/μs			
		3	V <sub>IPP</sub> = 2.5 V	−55°C		3.7					
				125°C		2					
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		25		nV/√ <del>Hz</del>			
			_	25°C		320					
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$			$V_O = V_{OH}$ , $R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 <sub>P</sub> F, See Figure 1	−55°C		400		kHz
			See rigule i	125°C		230					
				25°C		1.7					
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	−55°C		2.9		MHz			
		Occ rigure 3		125°C		1.1					
				25°C		46°					
$\phi_{\text{m}}$		$V_{\parallel} = 10 \text{ mV},$ $C_{\parallel} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	−55°C		49°					
		OL - 20 Pi ,	occ rigate 3	125°C		41°					

## operating characteristics at specified free-air temperature, $V_{DD}$ = 10 V

	DADAMETED		NETIONS	_	TLC274	4M, TLC	279M				
	PARAMETER	l lesi co	NDITIONS	TA	MIN	TYP	MAX	UNIT			
				25°C		5.3					
			V <sub>IPP</sub> = 1 V	−55°C		7.1					
0.0		$R_L = 10 \Omega$ ,		125°C		3.1		.,,			
SR	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		4.6		V/μs			
			V <sub>IPP</sub> = 5.5 V	−55°C		6.1					
				125°C		2.7					
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		25		nV/√ <del>Hz</del>			
				25°C		200					
ВОМ	Maximum output-swing bandwidth	VO = VOH,			$V_O = V_{OH}$ , $R_I = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	−55°C		280		kHz
			See rigule i	125°C		110					
				25°C		2.2					
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	−55°C		3.4		MHz			
		See Figure 3		125°C		1.6					
				25°C		49°					
$\phi_{m}$	Phase margin	$V_{l} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	−55°C		52°					
		OL = 20 PF,	See rigule 3	125°C		44°					

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## electrical characteristics, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

	DADAMETED	TEST SOME	SITIONS	Т	LC274Y		LINUT
	PARAMETER	TEST CONI	DITIONS	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$V_{O} = 1.4 \text{ V},$ $R_{S} = 50 \Omega,$	$V_{IC} = 0,$ $R_L = 10 \text{ k}\Omega$		1.1	10	mV
lιο	Input offset current (see Note 4)	V 05V			0.1		pА
I <sub>IB</sub>	Input bias current (see Note 4)	$V_{O} = 2.5 \text{ V},$	$V_{IC} = 2.5 V$		0.6		pА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 4	-0.3 to 4.2		٧
VOH	High-level output voltage	$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	3.2	3.8		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$	I <sub>OL</sub> = 0		0	50	mV
AVD	Large-signal differential voltage amplification	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 10 \text{ k}\Omega$	5	23		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$		65	80		dB
k <sub>SVR</sub>	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V <sub>O</sub> = 1.4 V	65	95		dB
I <sub>DD</sub>	Supply current (four amplifiers)	V <sub>O</sub> = 2.5 V, No load	V <sub>IC</sub> = 2.5 V,		2.7	6.4	mA

## electrical characteristics, $V_{DD}$ = 10 V, $T_A$ = 25°C (unless otherwise noted)

	DADAMETED	7507.00		Т	LC274Y		
	PARAMETER	TEST CONI	DITIONS	MIN	TYP	MAX	UNIT
V <sub>IO</sub>	Input offset voltage	$V_{O} = 1.4 \text{ V},$ $R_{S} = 50 \Omega,$	$V_{IC} = 0,$ $R_L = 10 \text{ k}\Omega$		1.1	10	mV
I <sub>IO</sub>	Input offset current (see Note 4)	., 5.,	.,		0.1		рΑ
I <sub>IB</sub>	Input bias current (see Note 4)	$V_{O} = 5 V$ ,	$V_{IC} = 5 V$		0.7		рΑ
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 9	-0.3 to 9.2		٧
VOH	High-level output voltage	$V_{ID} = 100 \text{ mV},$	R <sub>L</sub> = 10 kΩ	8	8.5		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$	I <sub>OL</sub> = 0		0	50	mV
AVD	Large-signal differential voltage amplification	$V_0 = 1 \text{ V to 6 V},$	R <sub>L</sub> = 10 kΩ	10	36		V/mV
CMRR	Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICR</sub> min		65	85		dB
ksvr	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V <sub>O</sub> = 1.4 V	65	95		dB
I <sub>DD</sub>	Supply current (four amplifiers)	V <sub>O</sub> = 5 V, No load	V <sub>IC</sub> = 5 V,		3.8	8	mA

<sup>5.</sup> This range also applies to each input individually.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## operating characteristics, $V_{DD}$ = 5 V, $T_A$ = 25°C

	PARAMETER	_	EST CONDITION	ue.	Т	LC274Y		LINUT
	PARAMETER	'	EST CONDITION	<b>V</b> 5	MIN	TYP	MAX	UNIT
CD	Clause at waits are in	$R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 pF,	V <sub>IPP</sub> = 1 V		3.6		Miss
SR	Slew rate at unity gain	See Figure 1		$V_{IPP} = 2.5 V$		2.9		V/μs
Vn	Equivalent input noise voltage	f = 1  kHz,	$R_S = 20 \Omega$ ,	See Figure 2		25		nV/√ <del>Hz</del>
ВОМ	Maximum output-swing bandwidth	V <sub>O</sub> = V <sub>OH</sub> , See Figure 1	$C_L = 20 pF$ ,	$R_L = 10 \text{ k}\Omega$ ,		320		kHz
B <sub>1</sub>	Unity-gain bandwidth	$V_I = 10 \text{ mV},$	C <sub>L</sub> = 20 <sub>P</sub> F,	See Figure 3		1.7		MHz
φm	Phase margin	V <sub>I</sub> = 10 mV, See Figure 3	$f = B_1$ ,	C <sub>L</sub> = 20 pF,		46°		

## operating characteristics, $V_{DD}$ = 10 V, $T_A$ = 25°C

	PARAMETER	_	TOT COMPITION	10	T	LC274Y		LINUT
	PARAMETER		EST CONDITION	15	MIN	TYP	MAX	UNIT
SR	Clauses at units agin	$R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 20 pF,	V <sub>IPP</sub> = 1 V		5.3		Muo
SK	Slew rate at unity gain	See Figure 1		V <sub>IPP</sub> = 5.5 V		4.6		V/µs
$v_n$	Equivalent input noise voltage	f = 1  kHz,	$R_S = 20 \Omega$ ,	See Figure 2		25		nV/√ <del>Hz</del>
ВОМ	Maximum output-swing bandwidth	V <sub>O</sub> = V <sub>OH</sub> , See Figure 1	C <sub>L</sub> = 20 pF,	$R_L = 10 \text{ k}\Omega$ ,		200		kHz
B <sub>1</sub>	Unity-gain bandwidth	$V_I = 10 \text{ mV},$	C <sub>L</sub> = 20 pF,	See Figure 3		2.2		MHz
φm	Phase margin	V <sub>I</sub> = 10 mV, See Figure 3	$f = B_1$ ,	$C_L = 20 pF$ ,		49°		

## PARAMETER MEASUREMENT INFORMATION

## single-supply versus split-supply test circuits

Because the TLC274 and TLC279 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

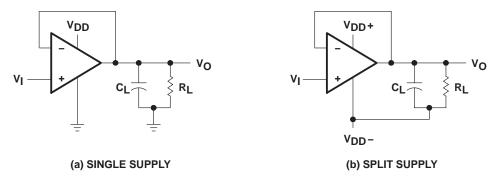


Figure 1. Unity-Gain Amplifier

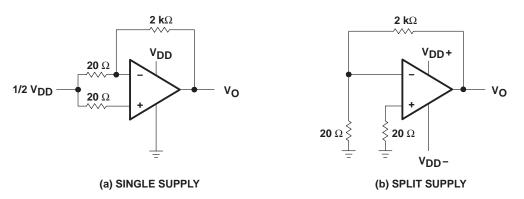


Figure 2. Noise-Test Circuit

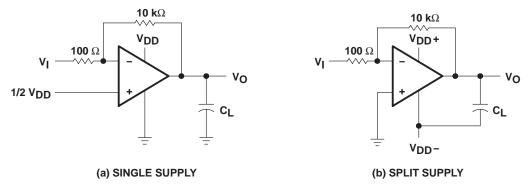


Figure 3. Gain-of-100 Inverting Amplifier

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## PARAMETER MEASUREMENT INFORMATION

## input bias current

Because of the high input impedance of the TLC274 and TLC279 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution: many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

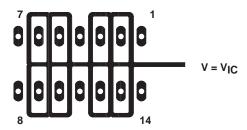


Figure 4. Isolation Metal Around Device Inputs (J and N packages)

## low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the Typical Characteristics of this data sheet.

## input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## PARAMETER MEASUREMENT INFORMATION

## full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.

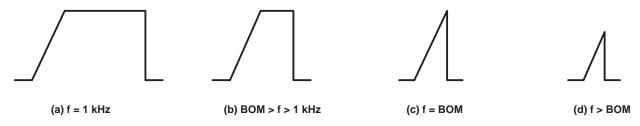


Figure 5. Full-Power-Response Output Signal

## test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## TYPICAL CHARACTERISTICS

## **Table of Graphs**

			FIGURE
۷ıO	Input offset voltage	Distribution	6, 7
ανιο	Temperature coefficient of input offset voltage	Distribution	8, 9
Vон	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V <sub>OL</sub>	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Large-signal differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I <sub>IB</sub>	Input bias current	vs Free-air temperature	22
lιΟ	Input offset current	vs Free-air temperature	22
VIС	Common-mode input voltage	vs Supply voltage	23
I <sub>DD</sub>	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
V <sub>O(PP)</sub>	Maximum peak-to-peak output voltage	vs Frequency	29
B <sub>1</sub>	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
φm	Phase margin	vs Supply voltage vs Free-air temperature vs Load capacitance	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37
	Phase shift	vs Frequency	32, 33

## TYPICAL CHARACTERISTICS

Percentage of Units - %

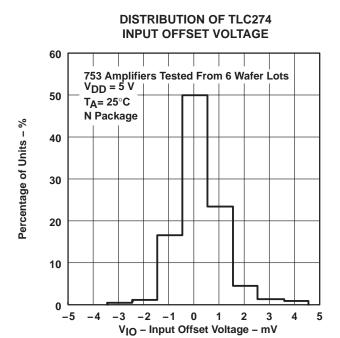


Figure 6

**DISTRIBUTION OF TLC274 AND TLC279** 

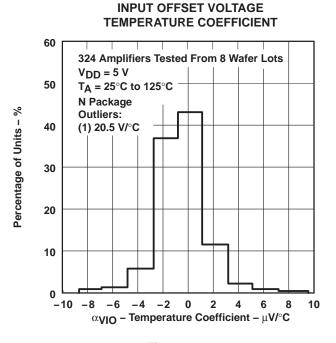


Figure 8

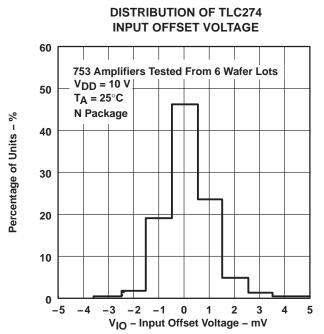


Figure 7

## DISTRIBUTION OF TLC274 AND TLC279 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

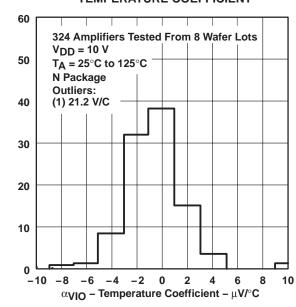


Figure 9

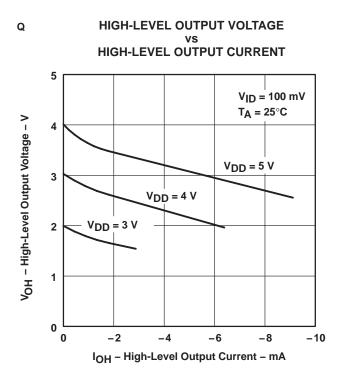


Figure 10

**HIGH-LEVEL OUTPUT VOLTAGE** 

**SUPPLY VOLTAGE** 

# 16 $V_{ID} = 100 \text{ mV}$ 14 $R_L = 10 \text{ k}\Omega$ $T_A = 25^{\circ}\text{C}$ 10 $R_L = 10 \text{ k}\Omega$ $R_L = 10 \text{ k}\Omega$

Figure 12

8

V<sub>DD</sub> - Supply Voltage - V

10

12

14

16

2



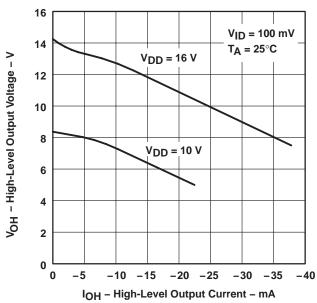


Figure 11

## HIGH-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

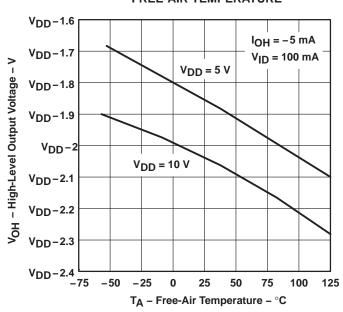


Figure 13

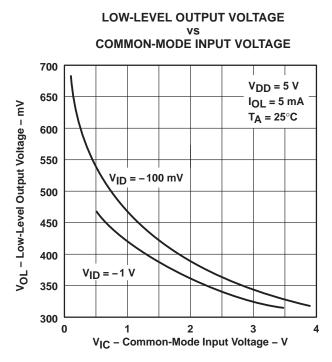


Figure 14

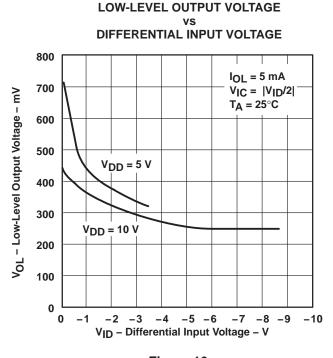


Figure 16

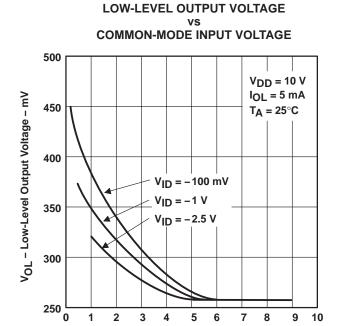


Figure 15

## LOW-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

V<sub>IC</sub> - Common-Mode Input Voltage - V

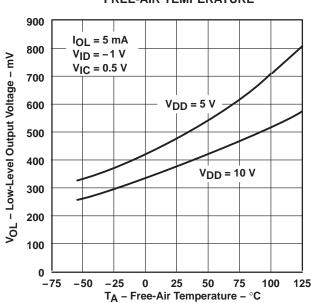


Figure 17

## LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

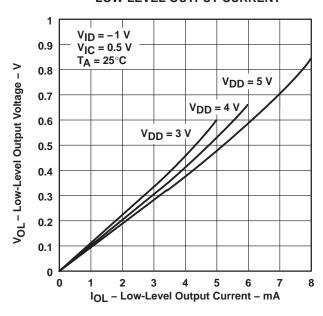


Figure 18

## LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION VS SUPPLY VOLTAGE

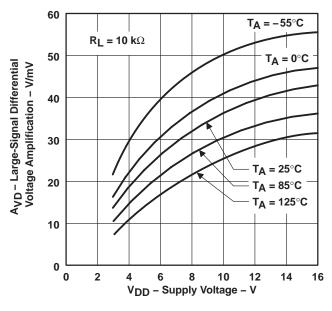


Figure 20

## LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

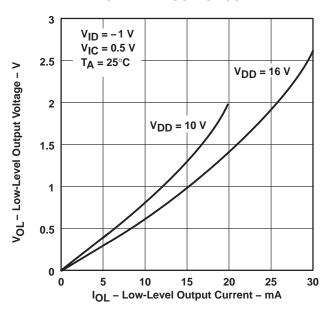


Figure 19

## LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION vs FREE-AIR TEMPERATURE

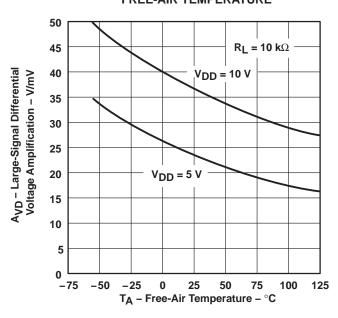
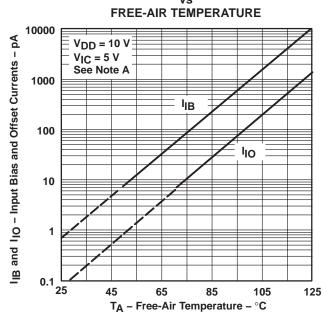


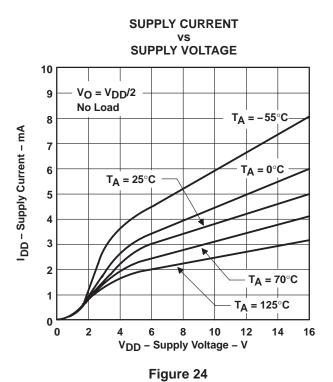
Figure 21

## INPUT BIAS CURRENT AND INPUT OFFSET CURRENT



NOTE A: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

## Figure 22



COMMON-MODE INPUT VOLTAGE POSITIVE LIMIT VS

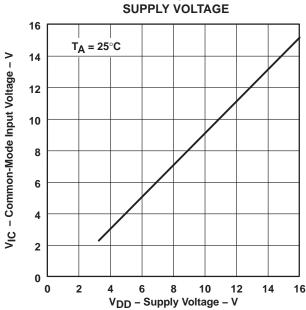


Figure 23

## SUPPLY CURRENT vs FREE-AIR TEMPERATURE

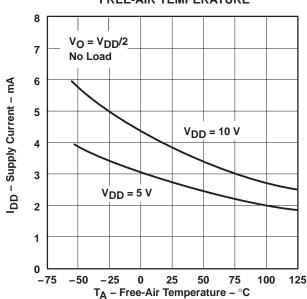


Figure 25

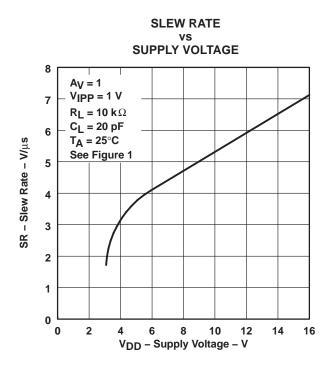


Figure 26

**NORMALIZED SLEW RATE** 

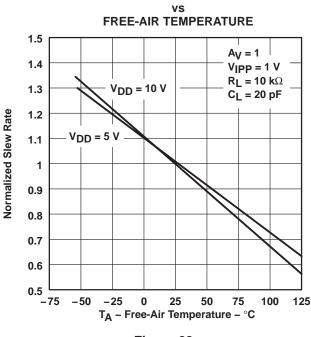


Figure 28

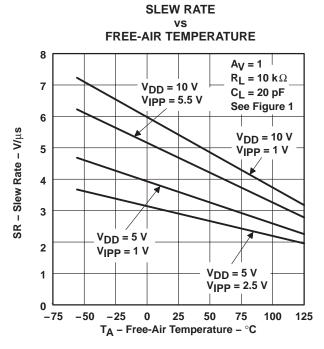


Figure 27

## MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE vs

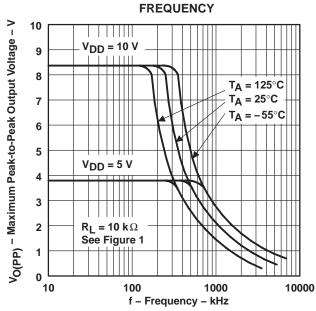
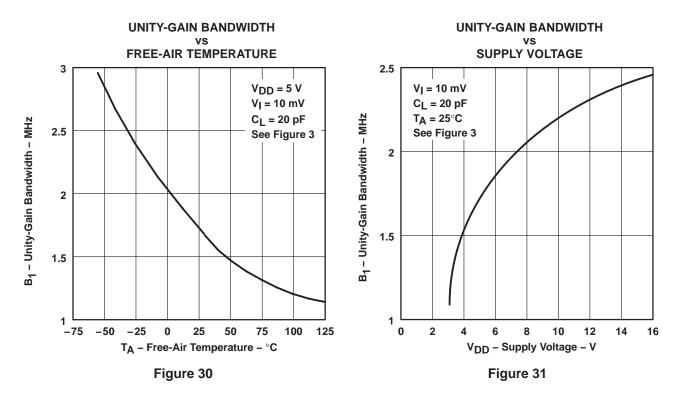


Figure 29



## LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

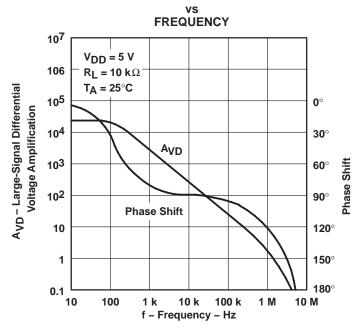


Figure 32

## LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

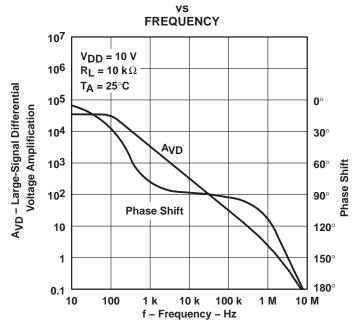
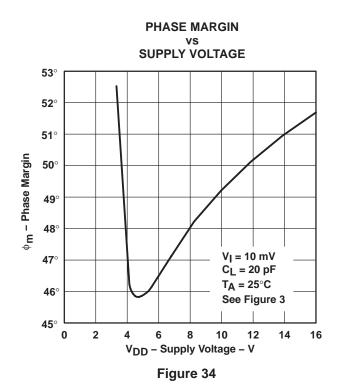
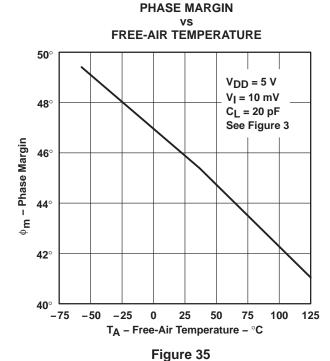
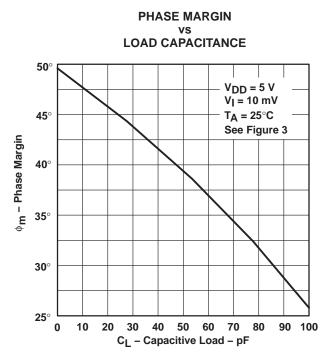


Figure 33





## **TYPICAL CHARACTERISTICS**





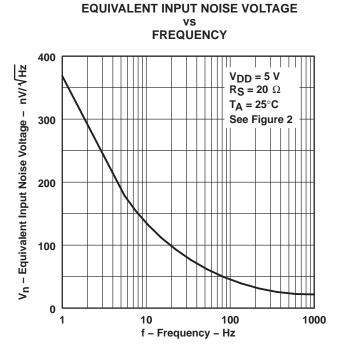


Figure 37

### **APPLICATION INFORMATION**

## single-supply operation

While the TLC274 and TLC279 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC274 and TLC279 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC274 and TLC279 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require R<sub>C</sub> decoupling.

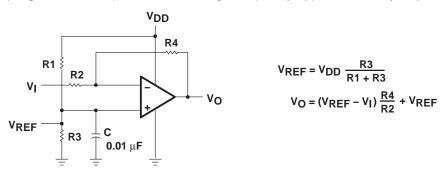


Figure 38. Inverting Amplifier With Voltage Reference

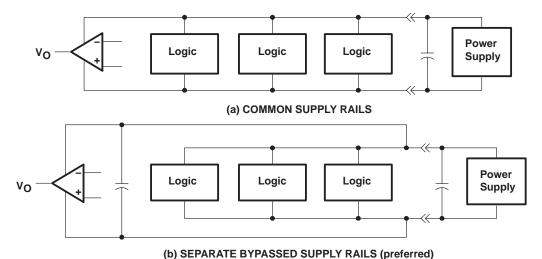


Figure 39. Common Versus Separate Supply Rails

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

### APPLICATION INFORMATION

## input characteristics

The TLC274 and TLC279 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at  $V_{DD} - 1$  V at  $T_A = 25^{\circ}$ C and at  $V_{DD} - 1.5$  V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC274 and TLC279 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1  $\mu$ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC274 and TLC279 are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

Unused amplifiers should be connected as grounded unity-gain followers to avoid possible oscillation.

## noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC274 and TLC279 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k $\Omega$ , since bipolar devices exhibit greater noise currents.

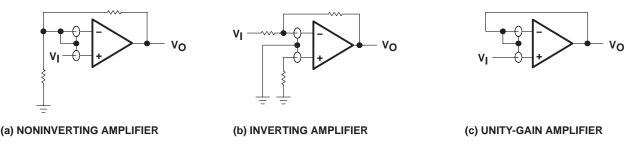


Figure 40. Guard-Ring Schemes

## output characteristics

The output stage of the TLC274 and TLC279 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC274 and TLC279 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.

(c) C<sub>L</sub> = 150 pF, R<sub>L</sub> = NO LOAD

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## **APPLICATION INFORMATION**

## output characteristics (continued)

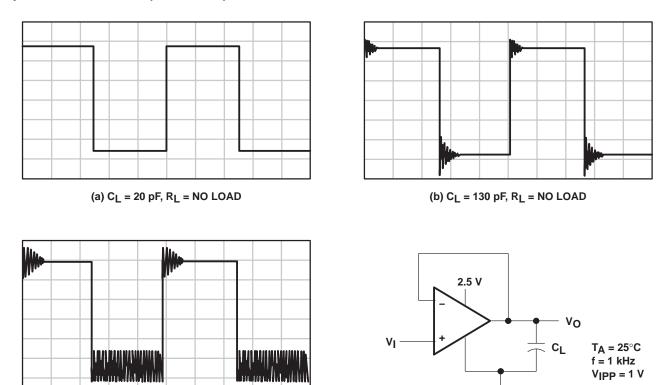


Figure 41. Effect of Capacitive Loads and Test Circuit

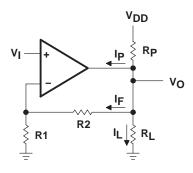
-2.5 V

(d) TEST CIRCUIT

Although the TLC274 and TLC279 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R<sub>P</sub>) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately  $60~\Omega$  and  $180~\Omega$ , depending on how hard the op amp input is driven. With very low values of R<sub>P</sub>, a voltage offset from 0 V at the output occurs. Second, pullup resistor R<sub>P</sub> acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.

### **APPLICATION INFORMATION**

## output characteristics (continued)



$$Rp = \frac{V_{DD} - V_{O}}{I_{E} + I_{I} + I_{D}}$$

Ip = Pullup current required by the operational amplifier (typically 500  $\mu$ A)

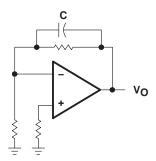


Figure 43. Compensation for Input Capacitance

## Figure 42. Resistive Pullup to Increase VOH

## feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

## electrostatic discharge protection

The TLC274 and TLC279 incorporate an internal electrostatic discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature-dependent and have the characteristics of a reverse-biased diode.

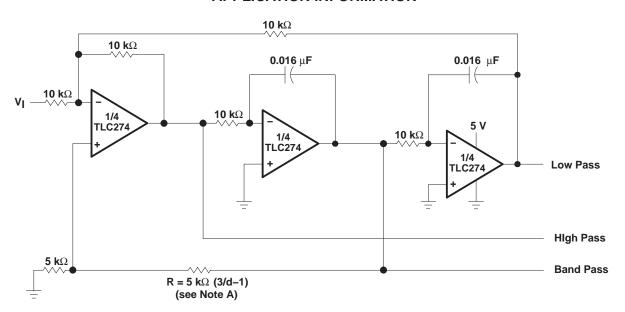
## latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC274 and TLC279 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1  $\mu$ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

SLOS092D - SEPTEMBER 1987 - REVISED MARCH 2001

## **APPLICATION INFORMATION**



NOTE A: d = damping factor, 1/Q

Figure 44. State-Variable Filter

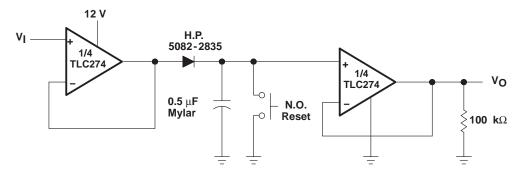
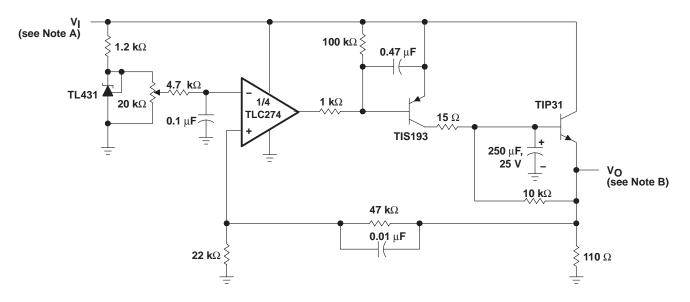


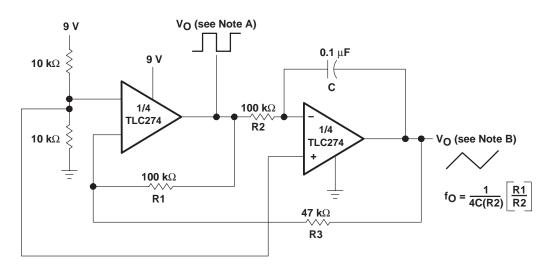
Figure 45. Positive-Peak Detector

## **APPLICATION INFORMATION**



NOTES: B.  $V_I = 3.5 \text{ V}$  to 15 V C.  $V_O = 2 \text{ V}$ , 0 to 1 A

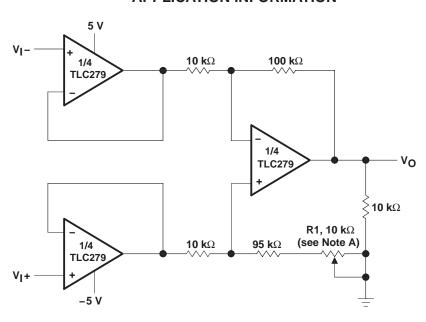
Figure 46. Logic-Array Power Supply



NOTES: A.  $V_{O(PP)} = 8 \text{ V}$ B.  $V_{O(PP)} = 4 \text{ V}$ 

Figure 47. Single-Supply Function Generator

## **APPLICATION INFORMATION**



NOTE C: CMRR adjustment must be noninductive.

Figure 48. Low-Power Instrumentation Amplifier

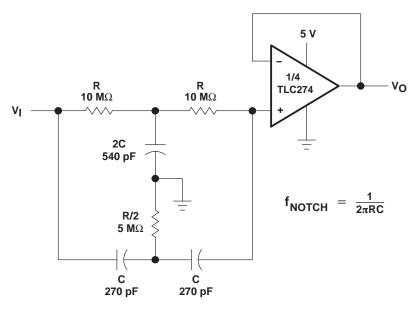


Figure 49. Single-Supply Twin-T Notch Filter

## **PACKAGE OPTION ADDENDUM**

14-Aug-2021

## **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLC274ACD	ACTIVE	SOIC	D	14	50	RoHS & Green	Call TI   NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274AC	Samples
TLC274ACDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274AC	Samples
TLC274ACN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC274ACN	Samples
TLC274ACNE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC274ACN	Samples
TLC274AID	ACTIVE	SOIC	D	14	50	RoHS & Green	Call TI   NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274AI	Samples
TLC274AIDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274AI	Samples
TLC274AIN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLC274AIN	Samples
TLC274BCD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274BC	Samples
TLC274BCDG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274BC	Samples
TLC274BCDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274BC	Samples
TLC274BCN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC274BCN	Samples
TLC274BCNE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC274BCN	Samples
TLC274BCNS	ACTIVE	so	NS	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274B	Samples
TLC274BID	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274BI	Samples
TLC274BIDG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274BI	Samples
TLC274BIDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274BI	Samples
TLC274BIDRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274BI	Samples
TLC274BIN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLC274BIN	Samples
TLC274CD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274C	Samples
TLC274CDB	ACTIVE	SSOP	DB	14	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	P274	Samples

## **PACKAGE OPTION ADDENDUM**

14-Aug-2021

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLC274CDBG4	ACTIVE	SSOP	DB	14	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	P274	Samples
TLC274CDBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	P274	Samples
TLC274CDG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274C	Samples
TLC274CDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274C	Samples
TLC274CDRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274C	Samples
TLC274CN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC274CN	Samples
TLC274CNE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC274CN	Samples
TLC274CNS	ACTIVE	SO	NS	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274	Samples
TLC274CNSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC274	Samples
TLC274CPW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	P274	Samples
TLC274CPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	P274	Samples
TLC274CPWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	P274	Samples
TLC274ID	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274I	Samples
TLC274IDG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274I	Samples
TLC274IDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC274I	Samples
TLC274IN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLC274IN	Samples
TLC274INE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLC274IN	Samples
TLC274IPW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	P274	Samples
TLC274IPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	Y274	Samples
TLC274IPWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	Y274	Samples
TLC274MD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	TLC274M	Samples

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
						.,	(6)	(-,		V /	
TLC274MDG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	TLC274M	Samples
TLC274MDRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	TLC274M	Samples
TLC279CD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC279C	Samples
TLC279CDG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC279C	Samples
TLC279CDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC279C	Samples
TLC279CN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TLC279CN	Samples
TLC279ID	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC279I	Samples
TLC279IDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC279I	Samples
TLC279IN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLC279IN	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

## TAPE AND REEL INFORMATION



## TAPE DIMENSIONS KO P1 BO W Cavity A0

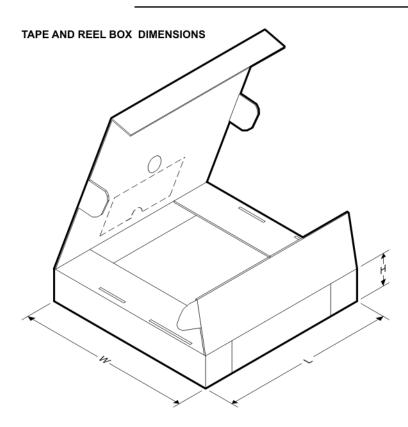
	Α0	Dimension designed to accommodate the component width
	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
г	D1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC274ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274BIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274CDBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.5	12.0	16.0	Q1
TLC274CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC274CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC274IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC274IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC274MDRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC279CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC279IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



\*All dimensions are nominal

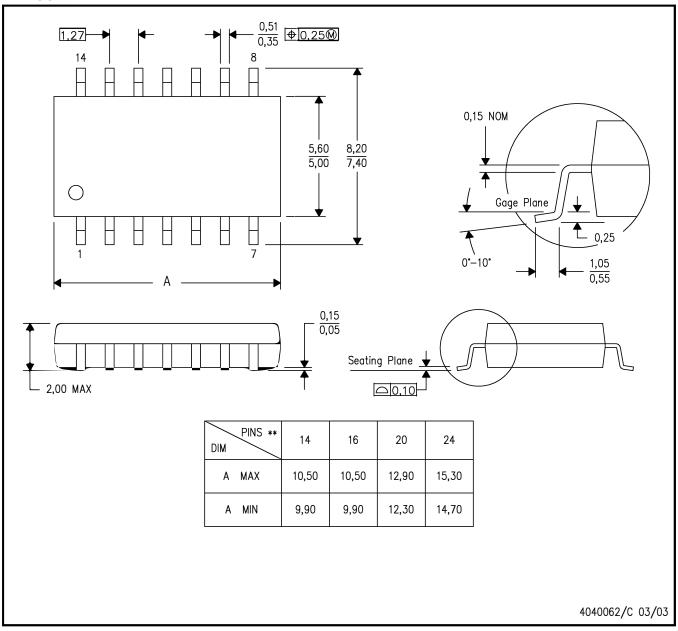
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TLC274ACDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC274ACDR	SOIC	D	14	2500	350.0	350.0	43.0	
TLC274AIDR	SOIC	D	14	2500	853.0	449.0	35.0	
TLC274AIDR	SOIC	D	14	2500	350.0	350.0	43.0	
TLC274BCDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC274BIDR	SOIC	D	14	2500	853.0	449.0	35.0	
TLC274CDBR	SSOP	DB	14	2000	853.0	449.0	35.0	
TLC274CDR	SOIC	D	14	2500	350.0	350.0	43.0	
TLC274CDR	SOIC	D	14	2500	853.0	449.0	35.0	
TLC274CDR	SOIC	D	14	2500	340.5	336.1	32.0	
TLC274CNSR	SO	NS	14	2000	853.0	449.0	35.0	
TLC274CPWR	TSSOP	PW	14	2000	853.0	449.0	35.0	
TLC274IDR	SOIC	D	14	2500	853.0	449.0	35.0	
TLC274IPWR	TSSOP	PW	14	2000	853.0	449.0	35.0	
TLC274MDRG4	SOIC	D	14	2500	350.0	350.0	43.0	
TLC279CDR	SOIC	D	14	2500	350.0	350.0	43.0	
TLC279IDR	SOIC	D	14	2500	350.0	350.0	43.0	

## **MECHANICAL DATA**

## NS (R-PDSO-G\*\*)

## 14-PINS SHOWN

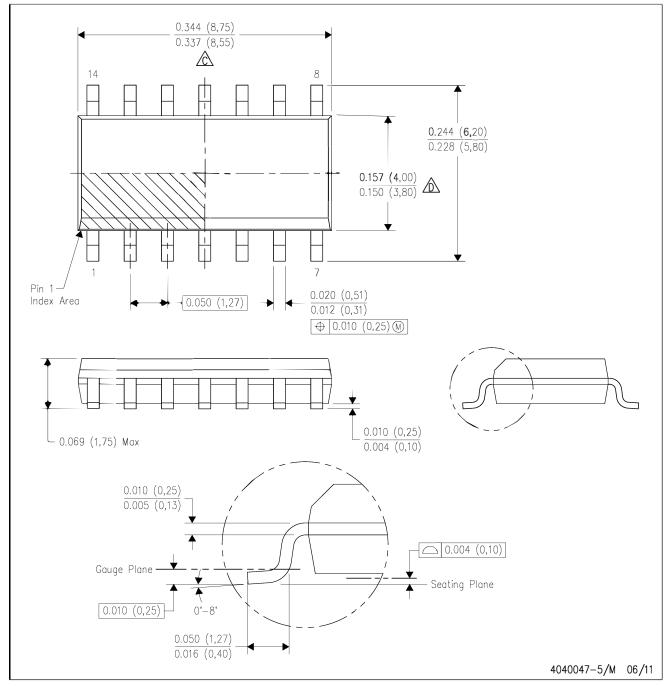
## PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

## D (R-PDSO-G14)

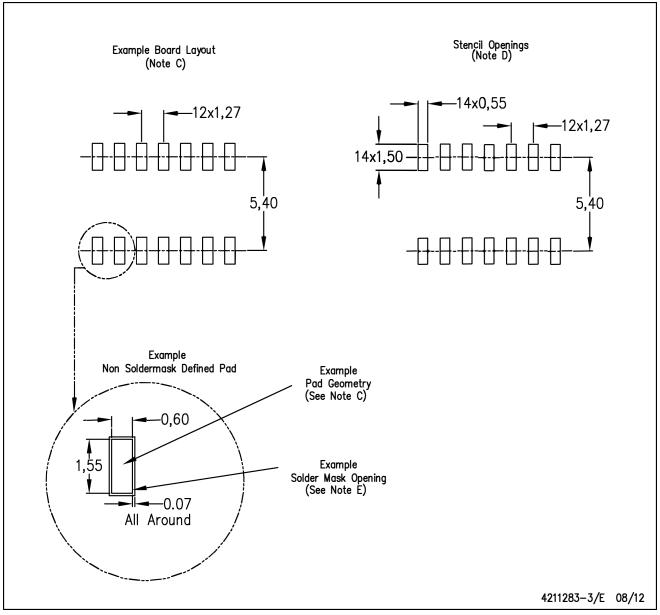
## PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.

## D (R-PDSO-G14)

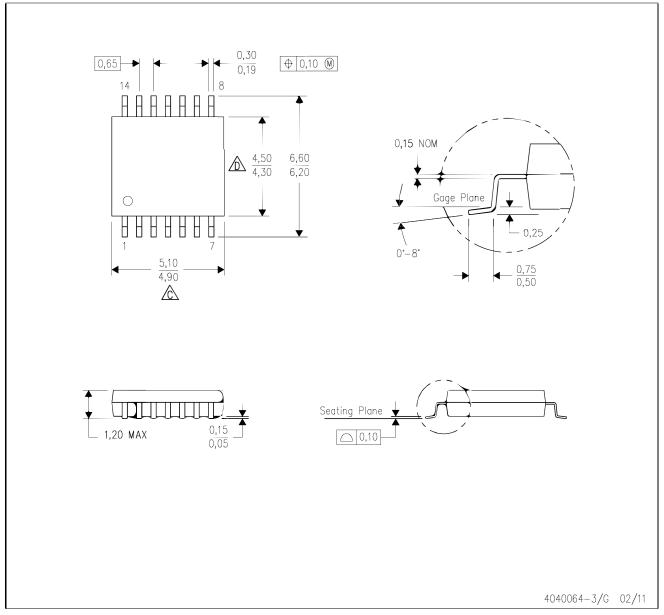
## PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R-PDSO-G14)

## PLASTIC SMALL OUTLINE

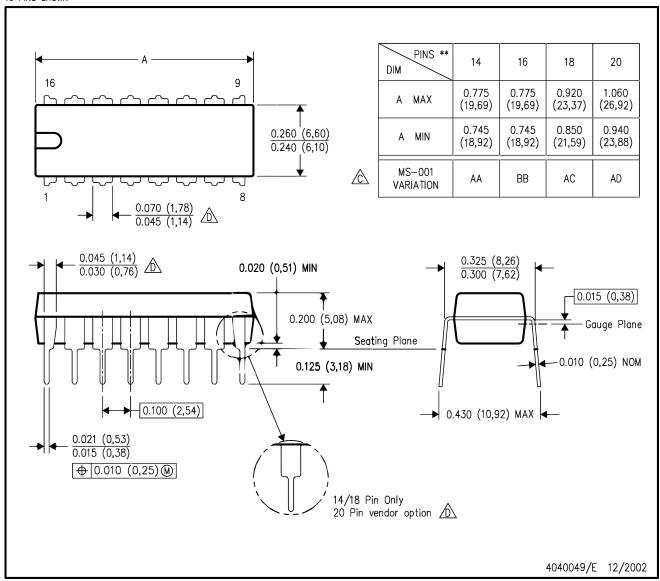


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153

## N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN

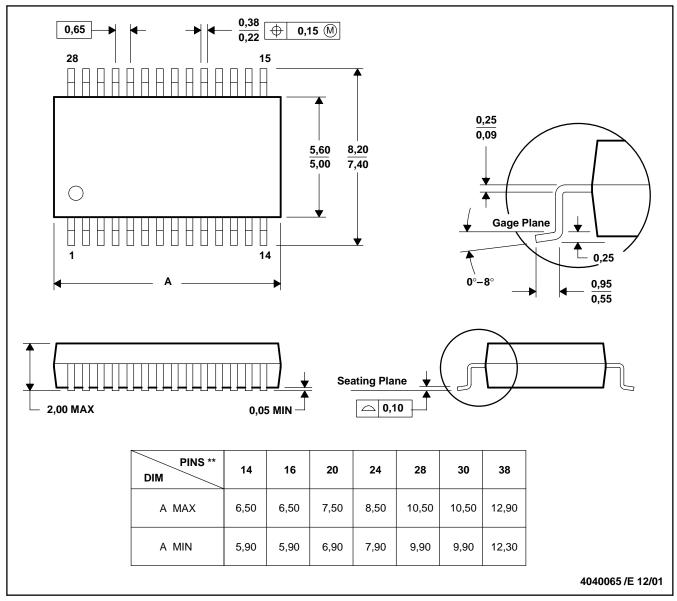


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.

## DB (R-PDSO-G\*\*)

## PLASTIC SMALL-OUTLINE

## **28 PINS SHOWN**



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-150